



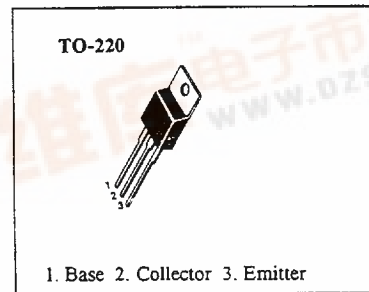
TIP127A PNP Epitaxial Silicon Transistor

MEDIUM POWER LINEAR SWITCHING APPLICATIONS

- Collector current 10A
- Collector dissipation $P_c = 75W$ ($T_c = 25\text{ }^\circ\text{C}$)

ABSOLUTE MAXIMUM RATINGS ($T_a = 25\text{ }^\circ\text{C}$)

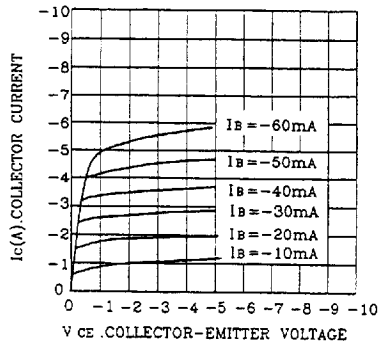
Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-20	V
Collector-Emitter Voltage	V_{CEO}	-10	V
Emitter-Base Voltage	V_{EBO}	-7	V
Collector Current	I_c	-10	A
Collector Dissipation	P_c	75	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ 150	$^\circ\text{C}$



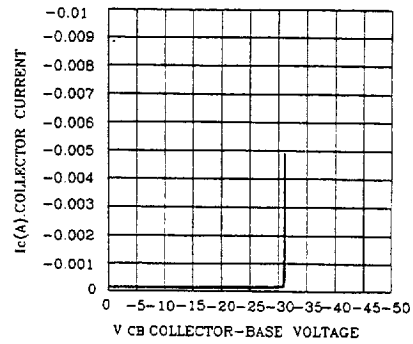
ELECTRICAL CHARACTERISTICS ($T_a = 25\text{ }^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_c = -1mA, I_E = 0$	-20			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_c = -10mA, I_B = 0$	-10			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -1mA, I_C = 0$	-7			V
Collector Cutoff Current	I_{CBO}	$V_{CB} = -15V, I_E = 0$			-100	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -3V, I_C = 0$			-100	μA
DC Current Gain	h_{FE1}	$V_{CE} = -3V, I_C = -6A$	80			
	h_{FE2}	$V_{CE} = -3V, I_C = -10A$	50			
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -6A, I_E = -600mA$			-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = -6A, V_{CB} = -4V$			-1.5	V

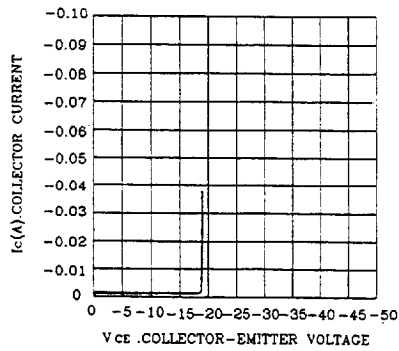
DC CURRENT GAIN



COLLECTOR-BASE BREAKDOWN VOLTAGE



COLLECTOR-EMITTER BREAKDOWN VOLTAGE



COLLECTOR-EMITTER SATURATION VOLTAGE

